

General Description

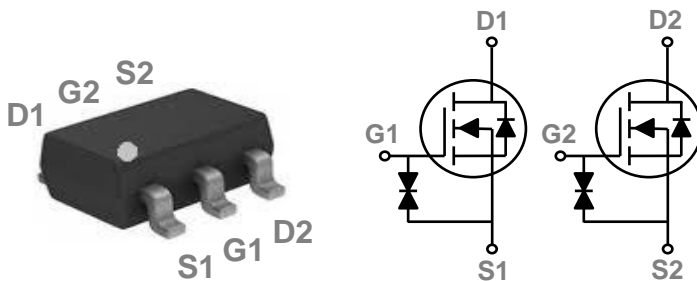
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDSON	ID
60V	3.5Ω	0.2A

Features

- 60V,0.2A, $R_{DS(ON)} = 3.5\Omega @ V_{GS} = 10V$
- Improved dv/dt capability
- Fast switching
- Green Device Available
- G-S ESD Protection Diode Embedded

SOT363 Dual Pin Configuration



Applications

- Notebook
- Load Switch
- Networking
- Hand-held Instruments

Absolute Maximum Ratings $T_c=25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous ($T_A=25^\circ C$)	0.2	A
	Drain Current – Continuous ($T_A=70^\circ C$)	0.16	A
I_{DM}	Drain Current – Pulsed ¹	0.8	A
P_D	Power Dissipation ($T_A=25^\circ C$)	278	mW
	Power Dissipation – Derate above 25°C	2.22	mW/°C
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	450	°C/W

Electrical Characteristics (T_J=25 °C, unless otherwise noted)
Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	60	---	---	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =60V, V _{GS} =0V, T _J =25°C	---	---	1	μA
		V _{DS} =48V, V _{GS} =0V, T _J =125°C	---	---	1	mA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±20	μA

On Characteristics

R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =0.2A	---	2.3	3.5	Ω
		V _{GS} =4.5V, I _D =0.1A	---	2.4	4	Ω
		V _{GS} =2.5V, I _D =0.1A	---	3.2	9	Ω
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250μA	0.9	1.35	1.8	V

Dynamic and switching Characteristics

Q _g	Total Gate Charge ^{2, 3}	V _{DS} =30V, V _{GS} =10V, I _D =0.1A	---	1	1.5	nC
Q _{gs}	Gate-Source Charge ^{2, 3}		---	0.05	0.1	
Q _{gd}	Gate-Drain Charge ^{2, 3}		---	0.5	0.75	
T _{d(on)}	Turn-On Delay Time ^{2, 3}	V _{DD} =30V, V _{GS} =10V, R _G =6Ω I _D =0.1A	---	5	10	ns
T _r	Rise Time ^{2, 3}		---	7	15	
T _{d(off)}	Turn-Off Delay Time ^{2, 3}		---	16	25	
T _f	Fall Time ^{2, 3}		---	12	20	
C _{iss}	Input Capacitance	V _{DS} =30V, V _{GS} =0V, F=1MHz	---	32	50	pF
C _{oss}	Output Capacitance		---	15	30	
C _{rss}	Reverse Transfer Capacitance		---	7.5	15	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	0.2	A
I _{SM}	Pulsed Source Current		---	---	0.4	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =0.2A, T _J =25°C	---	---	1	V
t _{rr}	Reverse Recovery Time	V _R =50V, I _S =0.2A	---	20	---	ns
Q _{rr}	Reverse Recovery Charge	di/dt=100A/μs, T _J =25°C	---	7.5	---	nC

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed, pulse width ≤ 300μs, duty cycle ≤ 2%.
3. Essentially independent of operating temperature.

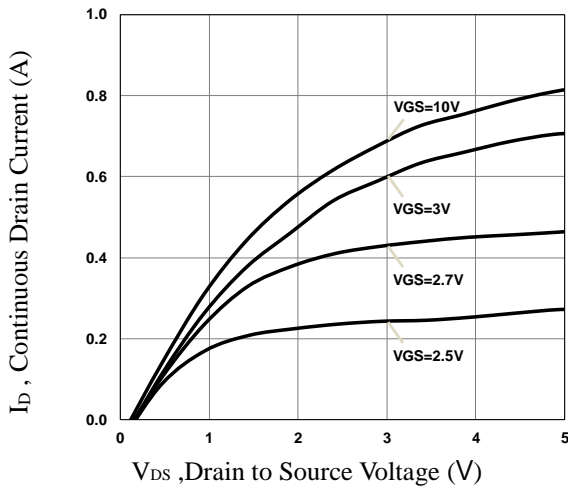


Fig.1 Typical Output Characteristics

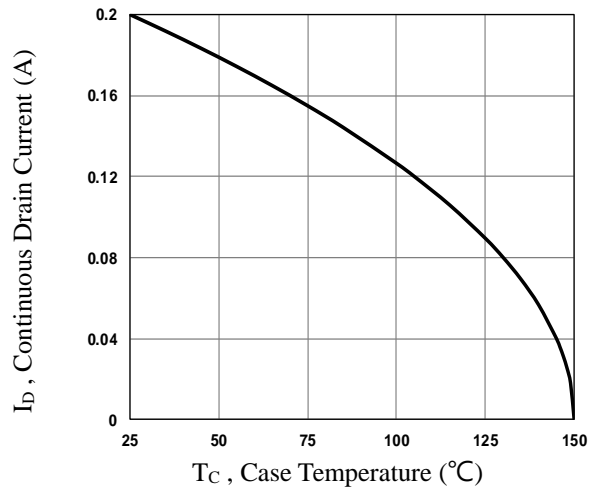


Fig.2 Continuous Drain Current vs. T_c

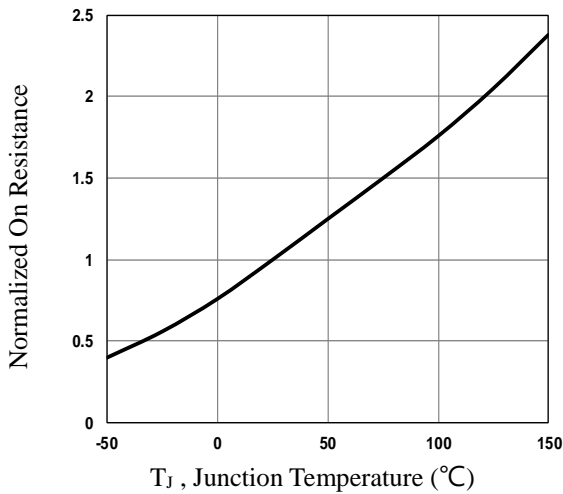


Fig.3 Normalized $R_{DS(on)}$ vs. T_j

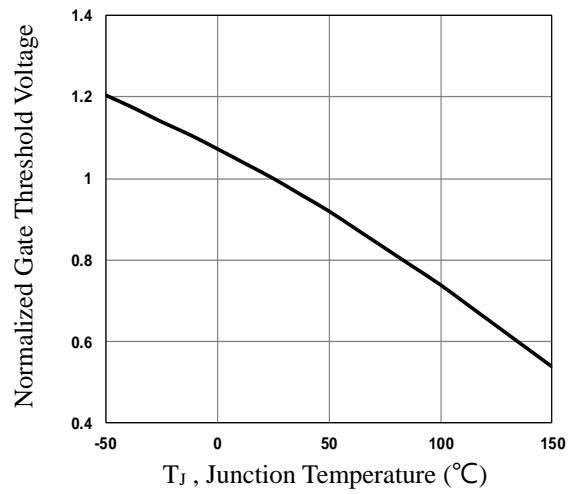


Fig.4 Normalized V_{th} vs. T_j

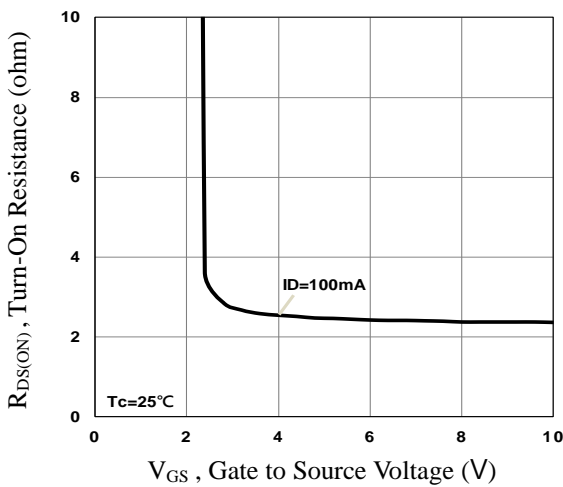


Fig.5 Turn-On Resistance vs. V_{GS}

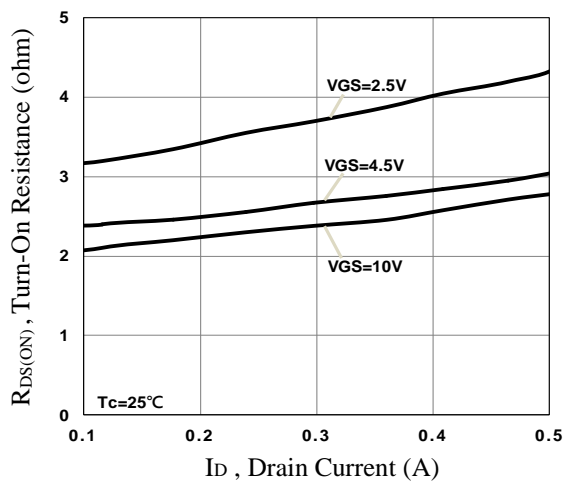


Fig.6 Turn-On Resistance vs. I_D

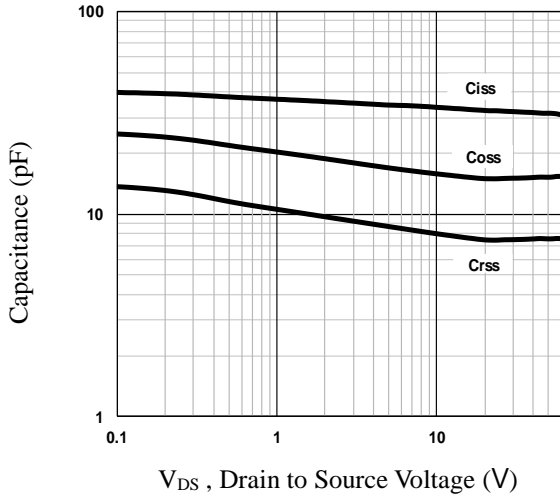


Fig.7 Capacitance Characteristics

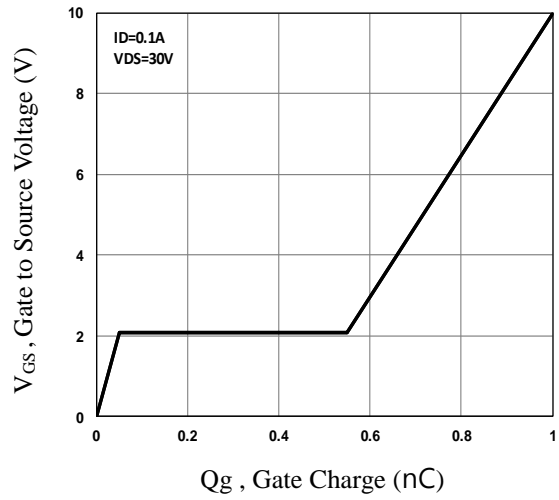


Fig.8 Gate Charge Characteristics

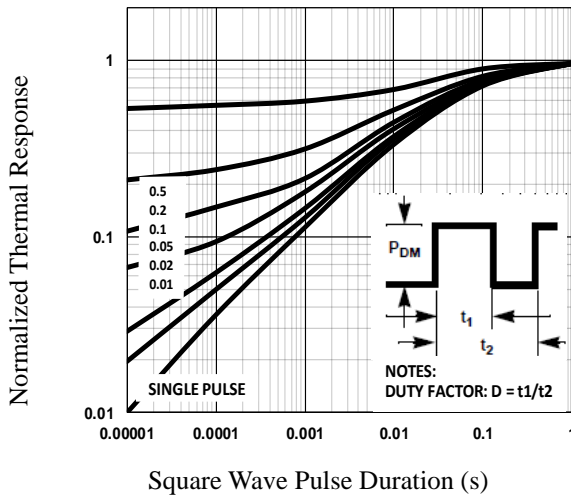


Fig.9 Normalized Transient Impedance

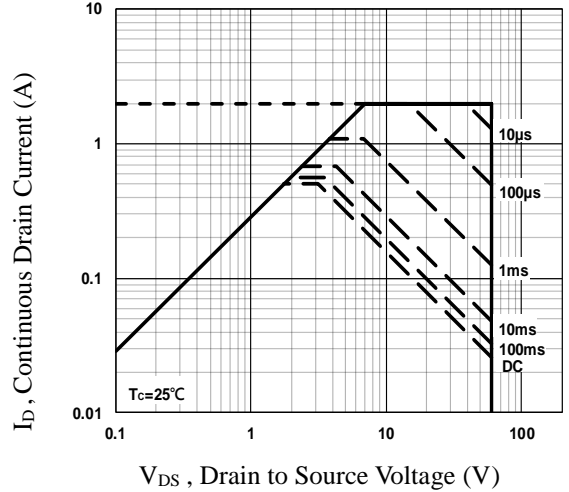


Fig.10 Maximum Safe Operation Area

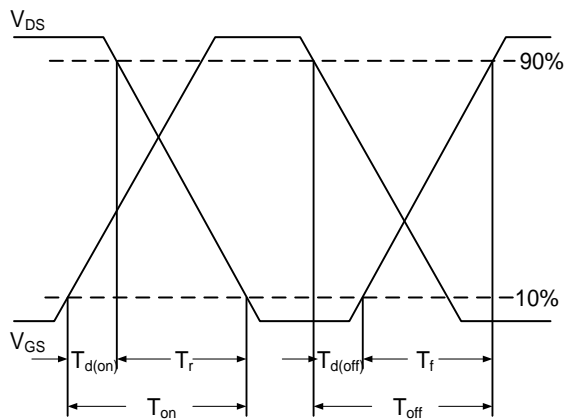


Fig.11 Switching Time Waveform

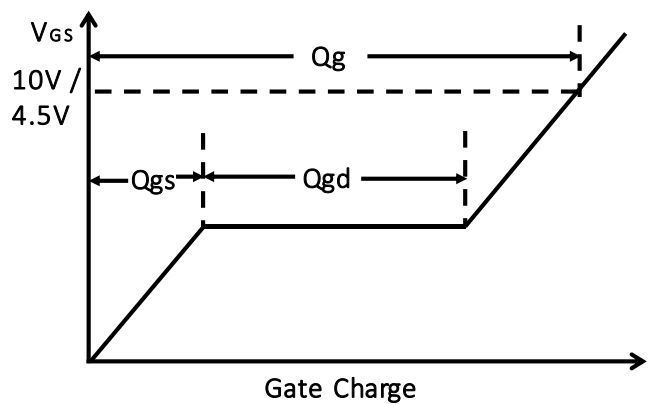
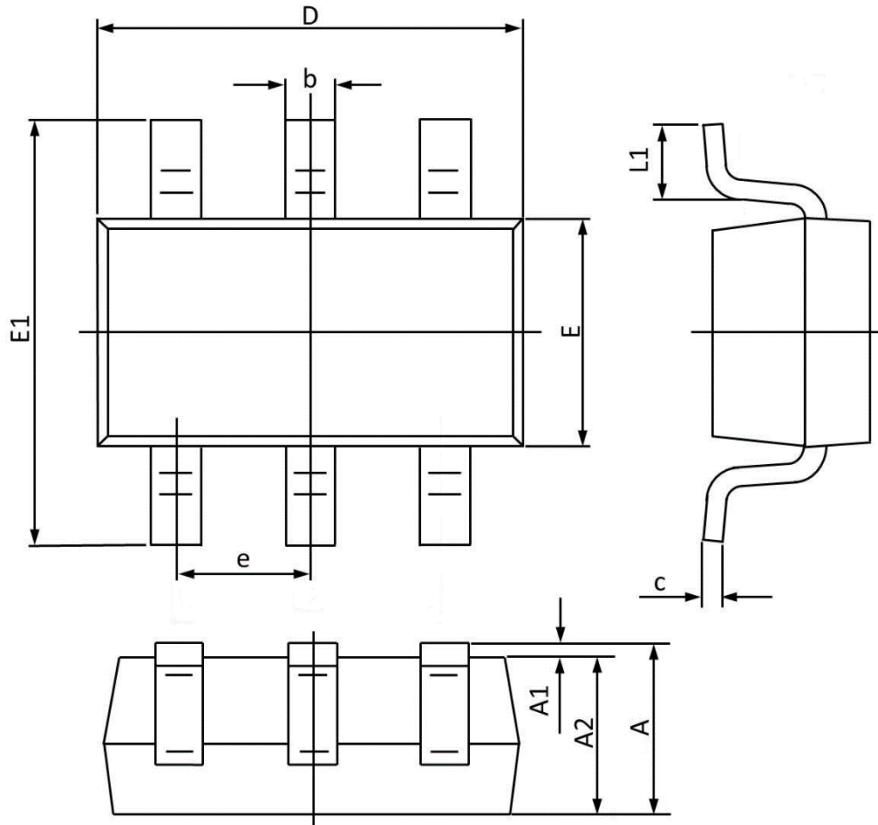


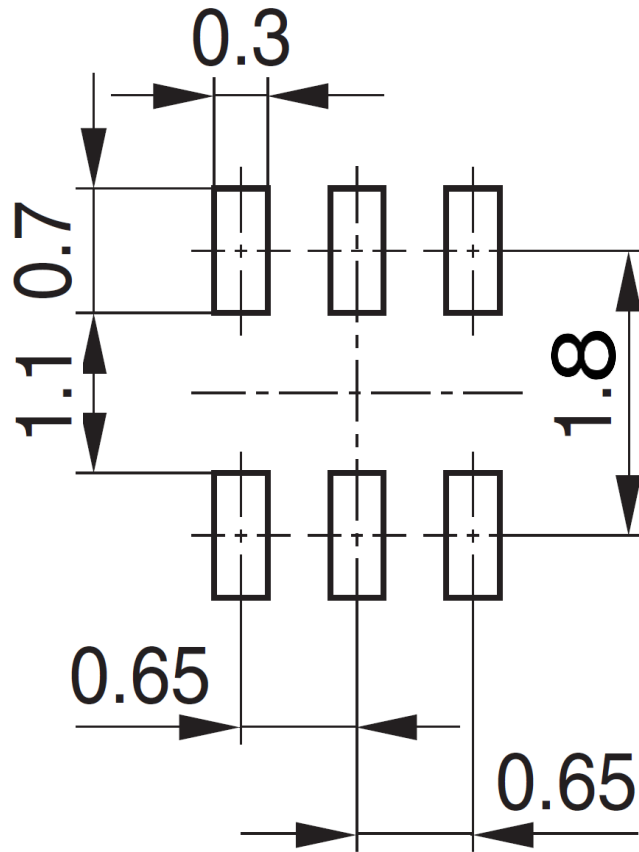
Fig.12 Gate Charge Waveform

SOT363 Dual PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	1.100	0.800	0.043	0.031
A1	0.100	0.000	0.004	0.000
A2	1.000	0.800	0.039	0.031
b	0.330	0.100	0.013	0.004
c	0.250	0.100	0.010	0.004
D	2.200	1.800	0.087	0.071
E	1.350	1.150	0.053	0.045
E1	2.400	1.800	0.094	0.071
e	0.65BSC		0.026BSC	
L1	0.350	0.100	0.014	0.004

SOT363 RECOMMENDED LAND PATTERN



unit : mm